

Dual 2-Input NAND Gate NLV27WZ00

The NLV27WZ00 is a high performance dual 2-input NAND Gate operating from a 1.65 V to 5.5 V supply.

Features

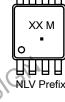
- Designed for 1.65 V to 5.5 V V_{CC} Operation
- 2.4 ns t_{PD} at $V_{CC} = 5 \text{ V (typ)}$
- Inputs/Outputs Overvoltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 24 mA at 3.0 V
- Available in US8 Package
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



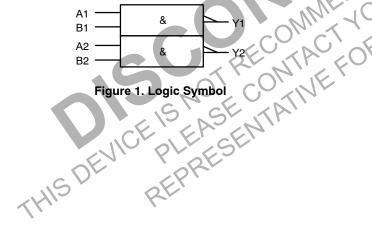
US8 **US SUFFIX CASE 493**



MARKING DIAGRAMS



X, XX, XXXX Specific Device Code Assembly Location Lot Code Year Code Week Code Date Code Pb-Free Package



ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

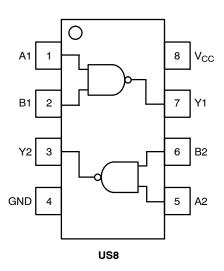


Figure 2. Pinout

PIN ASSIGNMENT (US8)

	Pin	Function	Inputs
	1	A1	A
	2	B1	10 6
	3	Y2	10 00
	4	GND	HIRORI
	5	A2	
	6	B2	H = HIGH Logic Level L = LOW Logic Level
	7	Y1	L = LOW Logic Level
	8	V _{CC}	TRENTE FO.
TH	SDEVI	SE IS NO.	SENTATIVE L= EUW Logic Level

FUNCTION TABLE
Y = AB

Inputs	Output
A B	$^{-}\mathcal{N}_{A}$
LO GE Y	(O, н
O, HVV	Н
H	Н
1 H 1	L

MAXIMUM RATINGS

Symbol	Chara	acteristics	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		−0.5 to +7.0	V
V _{OUT}	DC Output Voltage	Active–Mode (High or Low State) Tri–State Mode (Note 1) $Power$ – $Down Mode (V_{CC} = 0 V)$	-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0	V
I _{IK}	DC Input Diode Current	V _{IN} < GND	-50	mA
I _{OK}	DC Output Diode Current	V _{OUT} < GND	-50	mA
I _{OUT}	DC Output Source/Sink Current		±50	mA
I _{CC} or I _{GND}	DC Supply Current per Supply Pin or	Ground Pin	±100	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case to	for 10 secs	260	°C
TJ	Junction Temperature Under Bias		+150	7 ∘c
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	US8	250	°C/W
P_{D}	Power Dissipation in Still Air	US8	500	mW
MSL	Moisture Sensitivity		Level 1	-
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	-
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)	20,	5 <u>±</u> 100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Applicable to devices with outputs that may be tri-stated.
 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
- 4. Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit
V _{CC}	Positive DC Supply Voltage	1.65	5.5	V
V_{IN}	DC Input Voltage	0	5.5	V
V _{OUT}	DC Output Voltage Active-Mode (High or Low State) Tri-State Mode (Note 1) Power-Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Range	-55	+125	°C
t _r , t _f	Input Rise and Fall Time $V_{CC} = 1.65 \text{ V to } 1.95 \text{ V} \\ V_{CC} = 2.3 \text{ V to } 2.7 \text{ V} \\ V_{CC} = 3.0 \text{ V to } 3.6 \text{ V} \\ V_{CC} = 4.5 \text{ V to } 5.5 \text{ V} \\ \end{array}$	0 0 0	20 20 10 5	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DC ELECTRICAL CHARACTERISTICS

			V _{CC} T _A = 25°C		С	-55°C ≤ T	_A ≤ 125°C		
Symbol	Parameter	Condition	(V)	Min	Тур	Max	Min	Max	Units
V _{IH}	High-Level Input		1.65 to 1.95	0.75 x V _{CC}			0.75 x V _{CC}		V
	Voltage		2.3 to 5.5	0.70 x V _{CC}			0.70 x V _{CC}		
V _{IL}	Low-Level Input		1.65 to 1.95			0.25 x V _{CC}		0.25 x V _{CC}	V
	Voltage		2.3 to 5.5			0.30 x V _{CC}		0.30 x V _{CC}	
V _{OH}	High-Level Output Voltage	$\begin{split} V_{IN} &= V_{IH} \text{ or } V_{IL} \\ I_{OH} &= -100 \mu\text{A} \\ I_{OH} &= -4 \text{ mA} \\ I_{OH} &= -8 \text{ mA} \\ I_{OH} &= -12 \text{ mA} \\ I_{OH} &= -16 \text{ mA} \\ I_{OH} &= -24 \text{ mA} \\ I_{OH} &= -32 \text{ mA} \end{split}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	V _{CC} 1.4 2.1 2.4 2.7 2.5 4.0	- - - - -	V _{CC} - 0.1 1.29 1.9 2.2 2.4 2.3 3.8	- - - - -	٧
V _{OL}	Low-Level Output Voltage	$\begin{split} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 100 \mu\text{A} \\ &I_{OL} = 4 \text{ mA} \\ &I_{OL} = 8 \text{ mA} \\ &I_{OL} = 12 \text{ mA} \\ &I_{OL} = 16 \text{ mA} \\ &I_{OL} = 24 \text{ mA} \\ &I_{OL} = 32 \text{ mA} \end{split}$	1.65 to 5.5 1.65 2.3 2.7 3.0 3.0 4.5	- - - -	- 0.08 0.2 0.22 0.28 0.38 0.42	0.1 0.24 0.3 0.4 0.4 0.55 0.55		0.1 0.24 0.3 0.4 0.4 0.55 0.55	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	1.65 to 5.5	-		±0.1	-	±1.0	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V or V _{OUT} = 5.5 V	0		74	1.0	NON	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	MOF	2	1.0		10	μΑ

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

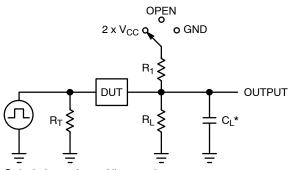
AC ELECTRICAL CHARACTERISTICS

				7	Γ _A = 25°(T _A = -55	to 125°C	
Symbol	Parameter	V _{CC} (V)	Test Conditions	Min	Тур	Max	Min	Max	Units
t _{PLH} ,	t _{PLH} , Propagation Delay, (A or B) to Y	1.65 to 1.95	C _L = 15 pF	-	5.7	10.5	-	11	ns
₹PHL		2.3 to 2.7	$R_L = 1 M\Omega$ $R_1 = Open$	i	3.2	5.3	_	5.7	
		3.0 to 3.6		- 2.4	3.7	_	4.0		
		4.5 to 5.5		-	1.9	2.9	-	3.2	
	3.0 to 3.6	C _L = 50 pF,	i	3.0	4.6	_	4.9		
		4.5 to 5.5	$R_L = 500 \Omega$, $R_1 = Open$	-	2.4	3.6	_	3.9	

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Units
C _{IN}	Input Capacitance	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0 \text{ V or } V_{CC}$	2.5	pF
C _{OUT}	Output Capacitance	$V_{CC} = 5.5 \text{ V}, V_{IN} = 0 \text{ V or } V_{CC}$	2.5	pF
C _{PD}	Power Dissipation Capacitance (Note 5)	10 MHz, V_{CC} = 3.3 V, V_{IN} = 0 V or V_{CC} 10 MHz, V_{CC} = 5.5 V, V_{IN} = 0 V or V_{CC}	9 11	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC} \cdot C_{PD}$ is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.



Test	Switch Position	C _L , pF	R_L, Ω	R ₁ , Ω
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table		
t _{PLZ} / t _{PZL}	2 x V _{CC}	50	500	500
t _{PHZ} / t _{PZH}	GND	50	500	500

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$

f = 1 MHz

Figure 3. Test Circuit

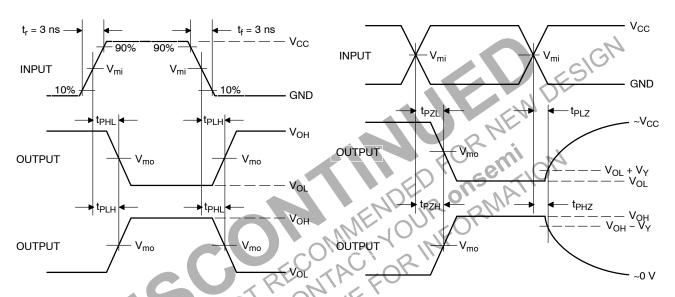


Figure 4. Switching Waveforms

	INCHAIR CE	V _m	, V	
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t_{PZL} , t_{PLZ} , t_{PZH} , t_{PHZ}	V _Y , V
1.65 to 1.95	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
2.3 to 2.7	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.15
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

DEVICE ORDERING INFORMATION

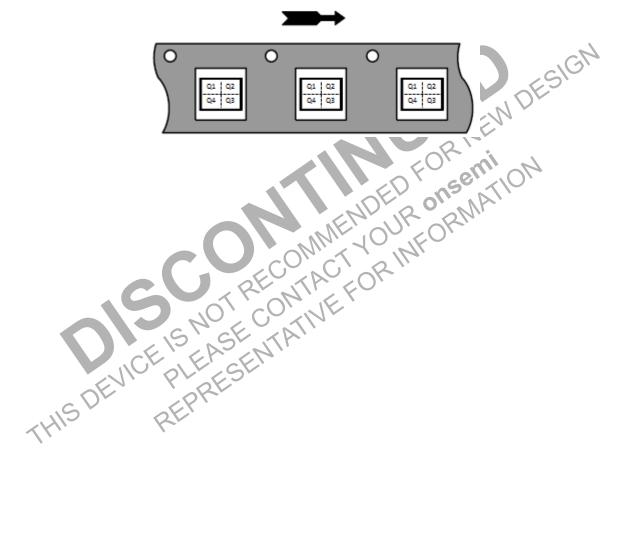
Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NL27WZ00USG-F22190	US8	L1	Q4	3000 / Tape & Reel
NLV27WZ00USG*	US8	L1	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel







^{*}NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

R R R R

В





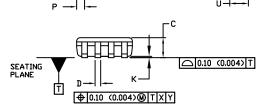
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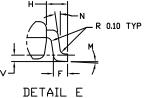
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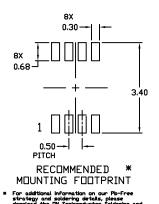
NOTES:

DETAIL E

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSION, OR GATE BURR. MOLD FLASH, PROTRUSION, OR GATE BURR SHALL NOT EXCEED 0.14 (0.0055°) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH AND PROTRUSION SHALL NOT EXCEED 0.14 (0.0055*) PER SIDE.
- LEAD FINISH IS SOLDER PLATING WITH THICKNESS OF 0.0076-0.0203 MM (0.003-0.008*).
- 6. ALL TOLERANCE UNLESS OTHERWISE SPECIFIED ±0.0508 MM (0.002").

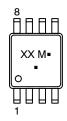






	MILLIMETERS		INCHES		
DIM	MIN.	MAX.	MIN.	MAX.	
Α	1.90	2.10	0.075	0.083	
В	2.20	2.40	0.087	0.094	
С	0.60	0.90	0.024	0.035	
D	0.17	0.25	0.007	0.010	
F	0.20	0.35	0.008	0.014	
G	0.50	BSC	0.020	BSC	
Н	0.40	REF	0.016 REF		
J	0.10	0.18	0.004	0.007	
К	0.00	0.10	0.000	0.004	
L	3.00	3.25	0.118	0.128	
М	0*	6*	0*	6*	
N	0*	10*	0*	10*	
Р	0.23	0.34	0.010	0.013	
R	0.23	0.33	0.009	0.013	
2	0.37	0.47	0.015	0.019	
U	0.60	0.80	0.024	0.031	
	0.12 BSC		0.005	BSC	

GENERIC MARKING DIAGRAM*



XX = Specific Device Code M = Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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